

## Supporting Information

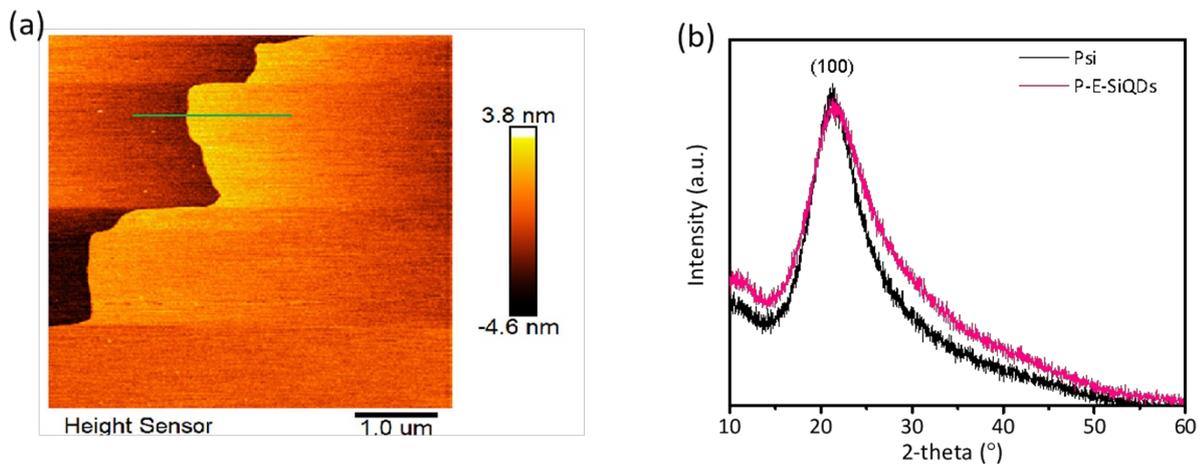
### Self-formed C-Dots-Based 2D Polysiloxane with High Photoluminescence Quantum Yield and Stability

Guangqi Hu<sup>1,2</sup>, Xiaokai Xu<sup>2</sup>, Bingfu Lei<sup>2</sup>, Jianle Zhuang<sup>2</sup>, Xuejie Zhang<sup>2</sup>, Haoran Zhang<sup>2</sup>, Chaofan Hu<sup>2</sup>, Xiaotang Liu<sup>2\*</sup>, Yingji He<sup>1\*</sup>, Yingliang Liu<sup>2\*</sup>

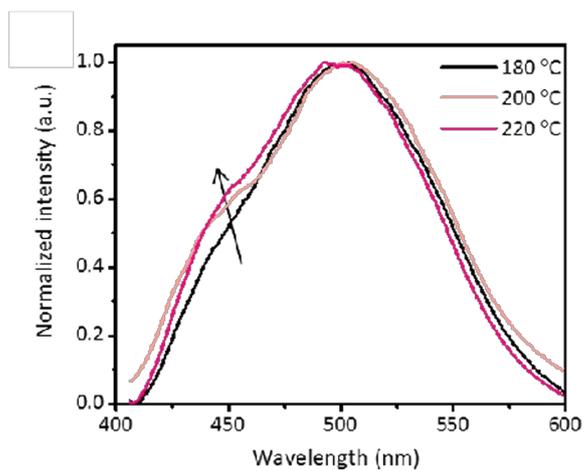
1\* School of Photoelectric Engineering, Guangdong Polytechnic Normal University, Guangzhou 510665, China

2\* College of Materials and Energy, South China Agricultural University, Guangzhou 510642, China

\*Email: [tliuyl@scau.edu.cn](mailto:tliuyl@scau.edu.cn).



**Figure S1.** (a) The representative AFM image of quasi-2-dimensional dual-fluorescence P-E-Si-CDs. (b) XRD patterns of Psi and dual-fluorescence P-E-Si-CDs.



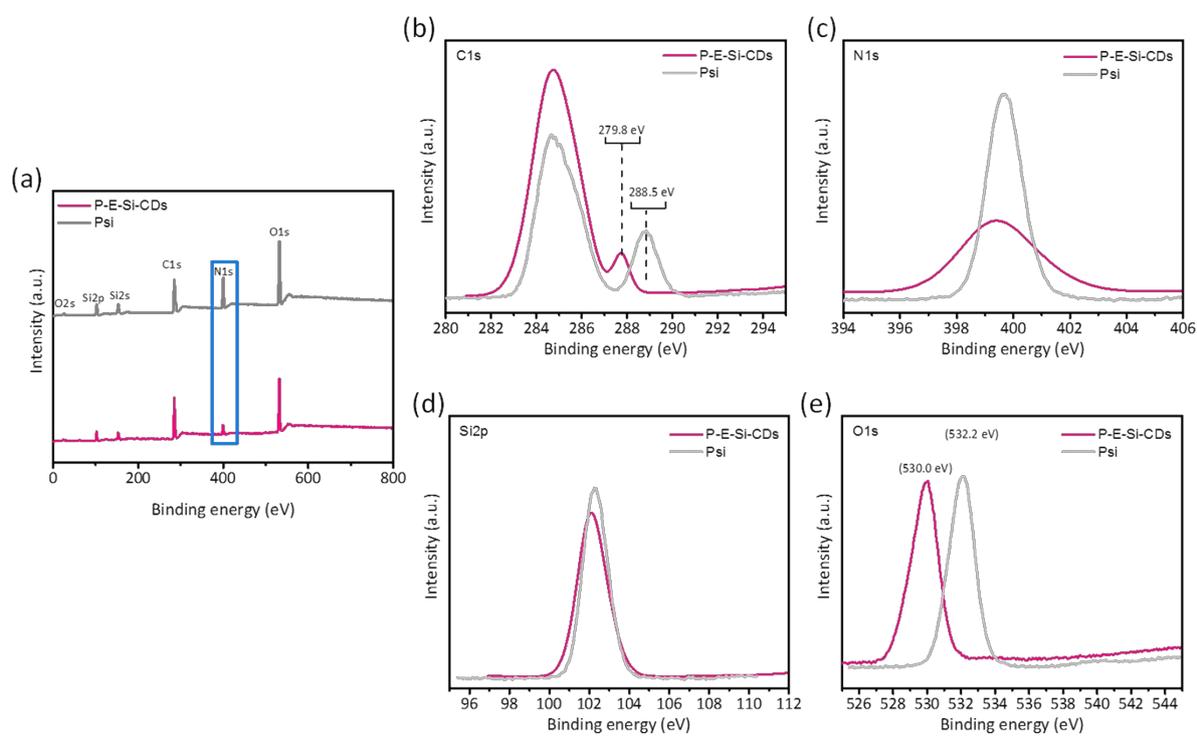
**Figure S2.** The fluorescence spectra of P-E-Si-CDs synthesized at different temperature under 395 nm excitation.

**Table S1.** Fitting results of the afterglow lifetimes of the P-E-Si-CDs at 440 nm and 515 nm under 395 nm excitation.

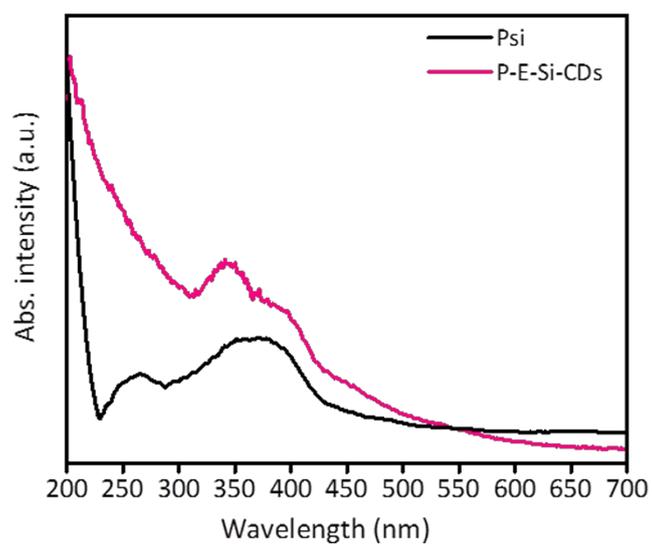
Emission(nm)	t1(ns)	B1(%)	t2(ns)	B2(%)	t <sub>avg</sub> (ns)
440	2.20	40.62	1.63	59.38	1.86
515	7.04	27.37	2.81	72.63	3.97

**Table S2.** EDS-analysed element contents of C, N, O, S in Psi and dual-fluorescence P-E-Si-CDs.

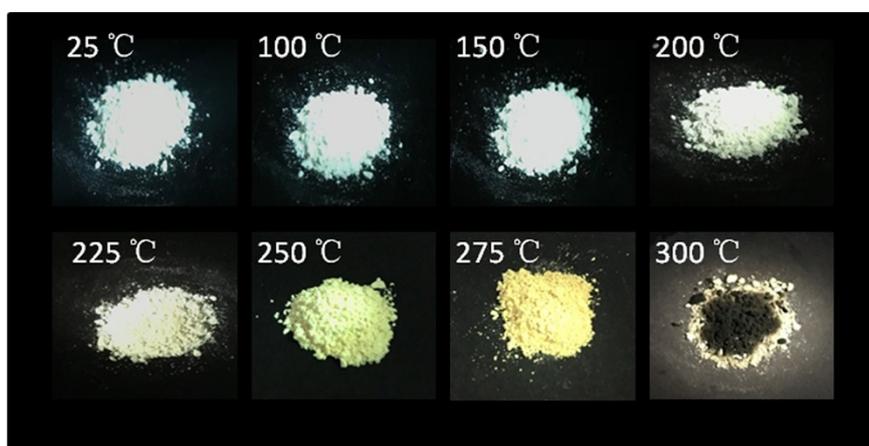
Elements	Psi	P-E-Si-CDs
C	43.98	56.36
N	18.54	7.93
O	24.98	23.48
Si	12.50	12.23



**Figure S3.** (a) XPS spectra, High-resolution XPS (b) C1s, (c) N1s, (d) Si2p and (f) O1s spectra of Psi and dual-fluorescence P-E-Si-CDs.

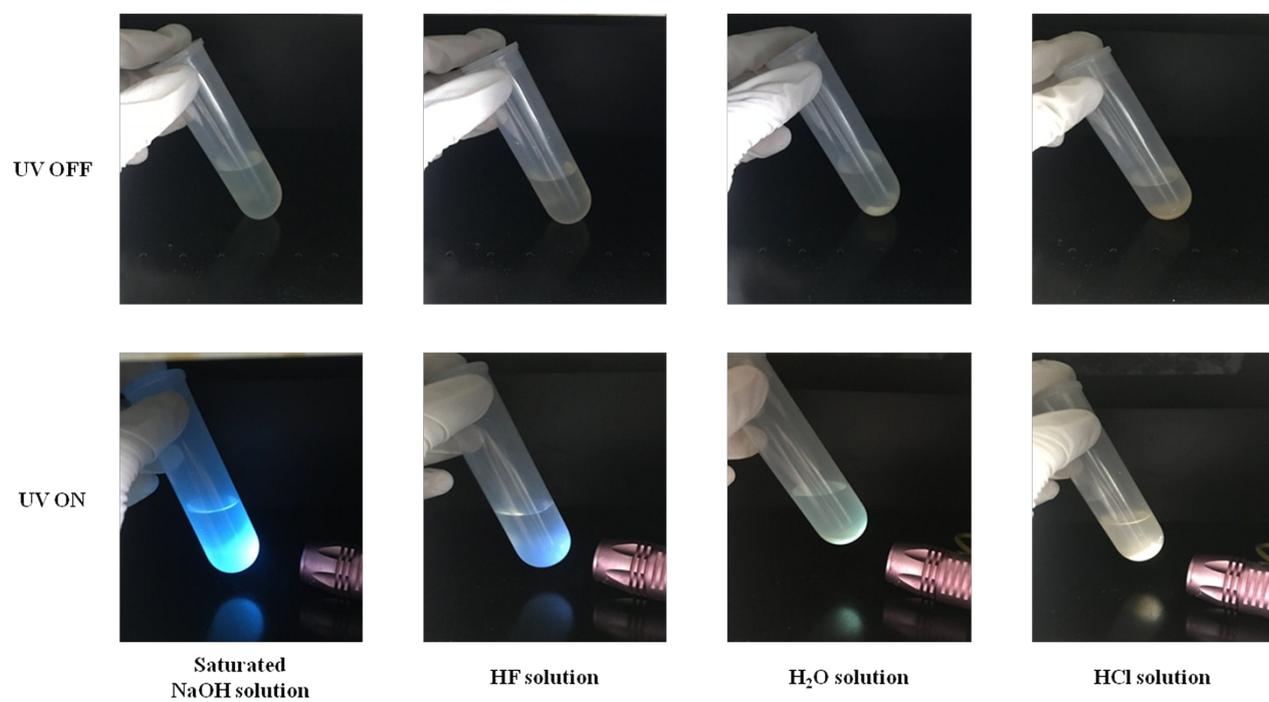


**Figure S4.** UV-Vis absorption spectra of Psi and dual-fluorescence P-E-Si-CDs.

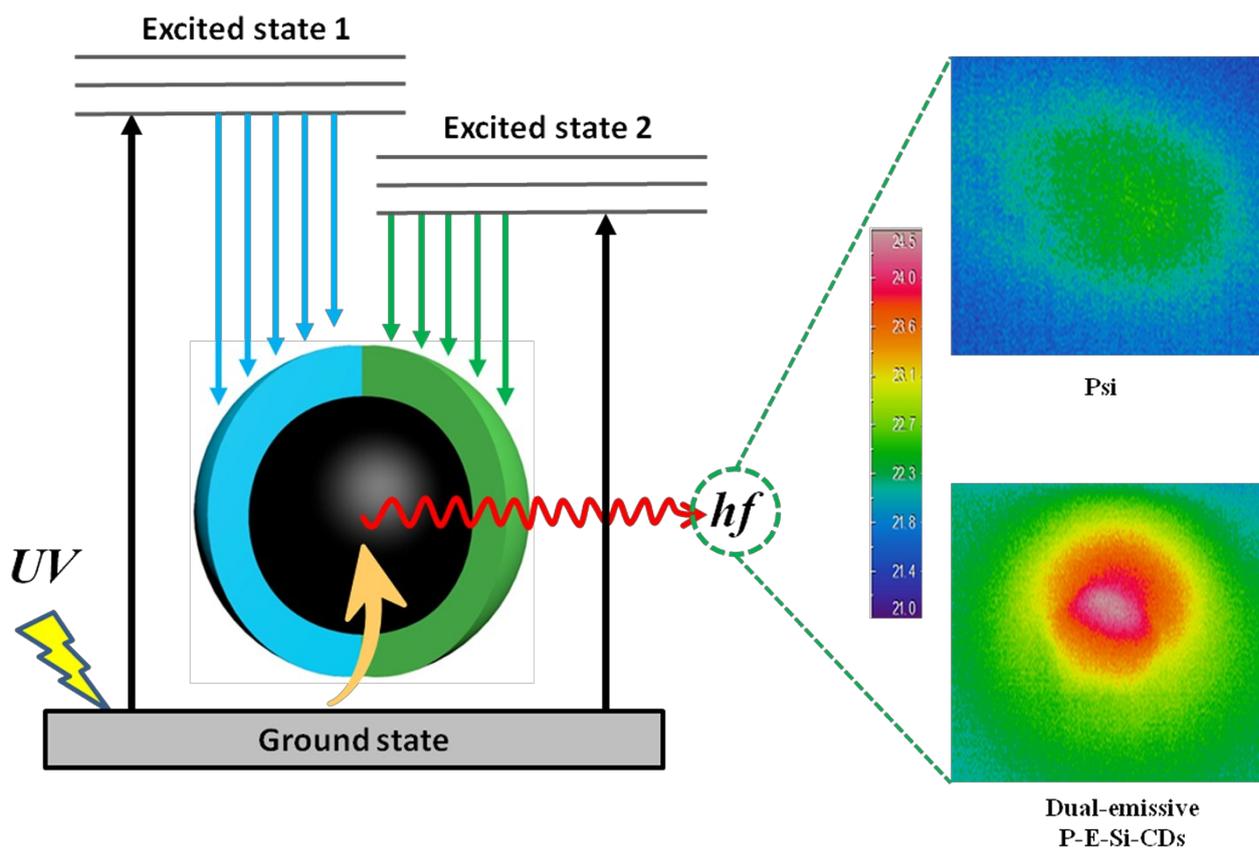


**Figure S5.** The fluorescence photographs under the varying treated temperature.

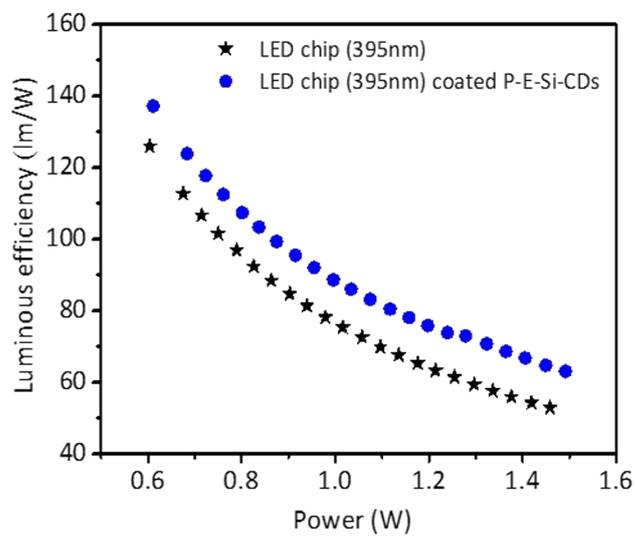




**Figure S6.** Photographs of P-E-Si-CDs in saturated NaOH solution, HF solution, water and concentrated HCl (37%) under UV irradiation or not.



**Figure 7.** The mechanism illustration of P-E-Si-CDs with the function of UV absorption (Left), and the infrared images (right) of Psi and dual-fluorescence P-E-Si-CDs.



**Figure S8.** Luminous efficiency of warm WLED based on UV-emissive LED chip ( $\lambda_{\text{peak}}$ : 395 nm) and dual-fluorescence P-E-Si-CDs along with varying electric power.